

**METHOD FOR OBTAINING ELLIPTICAL AND ROUNDED SHAPES USING
BEAM SHAPING**

5 ABSTRACT

 A method of fabricating a mask (316) for patterning
a semiconductor wafer. The mask (316) includes
elliptical (340) or rounded features formed using an
elliptical-shaped energy beam (350). Undesired stair-
10 step shaped edges (344) of the oval (340) or rounded
features formed by using a substantially circular-shaped
energy beam to form the oval or rounded features are
smoothed with the elliptical-shaped energy beam (350). A
method of fabricating a semiconductor device with the
15 mask (316) is included. The elliptical-shaped energy
beam (350) may also be used to directly pattern a
semiconductor wafer.